Abstracts

X and Ku Band High Power GaAs FETs

Y. Yamada, H. Kuroda, H. Izumi, T. Soezima, H. Wakamatsu and S. Hori. "X and Ku Band High Power GaAs FETs." 1988 MTT-S International Microwave Symposium Digest 88.2 (1988 Vol. II [MWSYM]): 847-850.

Internally matched GaAs FETs, with output powers of more than 10W, have been developed for the 10.7-11.7 and 14.0-14.5 GHz bands. These devices, with a total gate width of 32mm, consist of two chips that are fabricated by direct ion implantation and chemical dry etching. At 14.25 GHz, the Ku band device has achieved an output power of 41dBm, a power gain of 5 dB and a power added efficiency of 21%. At 11.2 GHz, the X band device has delivered 41.2 dBm, 5.8 dB and 25% respectively at the 1 dB gain compression point.

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